

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. **(Currently Amended)** A cleaning solution for surface treatment operations in which metal impurity contamination becomes troublesome comprising an alkaline compound, hydrogen peroxide, water and 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris] and/or or 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and nitrilotriacetic acid [NTA; CAS 139-13-9; Titrplex I] as chelating additive(s).
2. **(Currently Amended)** A cleaning solution according to claim 1, wherein characterised in that the alkaline compound is chosen from the group consisting of an organic base, ammonia, ammonium hydroxide, or tetramethyl ammonium hydroxide.
3. **(Currently Amended)** A cleaning solution according to claim 1, wherein characterised in that the alkaline compound is chosen from the group consisting of ammonia and or ammonium hydroxide.
4. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris] in an amount in the range of 1000 to 3000 ppm.
5. **(Currently Amended)** A cleaning solution according to claim 1, comprising nitrilotriacetic acid[NTA; CAS 139-13-9; Titrplex I] in an amount in the range of 100 to 2000 ppm.
6. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris] and nitrilotriacetic acid [NTA; CAS 139-13-9; Titrplex I] in a total amount less than 4000 ppm.
7. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris] and nitrilotriacetic acid [NTA; CAS 139-13-9; Titrplex I] in a total amount less than 2000 ppm.

8. **(Currently Amended)** A method for cleaning a semiconductor substrate substrate(s) comprising the step of treatment of treating the semiconductor substrate substrate(s) with a cleaning solution according to claim 1, and drying said semiconductor substrate substrate(s) after water rinsing.
9. **(Currently Amended)** A method of treatment according to claim 8, wherein characterised in that the treatment with cleaning solution is carried out at a temperature the range of 20 to 80 °C.
10. **(Currently Amended)** A method of treatment according to claim 8, wherein characterised in that the treatment with cleaning solution is carried out at normal room temperature.
11. **(Currently Amended)** A method of treatment according to claim 8, wherein characterised in that said cleaning solution is solutions according to the invention are brought into contact with a surface surfaces to be cleaned for a few seconds to 60 minutes.
12. **(Currently Amended)** A method of treatment according to claim 8, wherein characterised in that said cleaning solution is solutions according to the invention are brought into contact with a surface surfaces to be cleaned for about 15 seconds to 15 minutes.
13. **(Currently Amended)** A method for treatment of a semiconductor substrate substrate(s) according to claim 8, wherein the semi-conductor substrate substrate(s) is (are) immersed / dipped in the cleaning solution (called dipping type cleaning).
14. **(Currently Amended)** Use A method for cleaning solutions according to claim 1 ~~for~~ ~~for~~ surface treatment operations including cleaning, etching, polishing, film-forming, for the cleaning of substrates such as semiconductor, metal, glass, ceramics, plastic, magnetic material, superconductors comprising contacting said surface with a cleaning solution according to claim 1.